

80V N-Channel Enhancement Mode Power MOSFET

Description

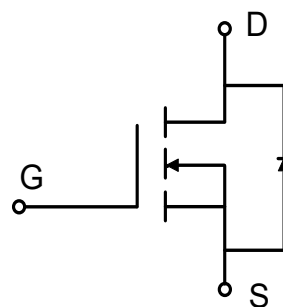
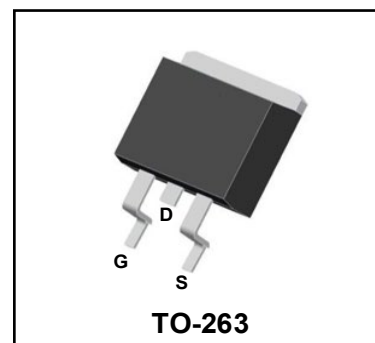
WMM80N08TS uses advanced power trench technology that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Features

- $V_{DS} = 80V$, $I_D = 80A$
 $R_{DS(on)} < 12m\Omega$ @ $V_{GS} = 10V$
- Green Device Available
- Low Gate Charge
- Advanced High Cell Density Trench Technology
- 100% EAS Guaranteed

Applications

- Synchronous Rectification
- DC/DC Converter
- Motor Control

Absolute Maximum Ratings (T_c = 25°C, unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T _c =25°C	I_D	80	A
	T _c =100°C		50.6	
Pulsed Drain Current ⁴		I_{DM}	320	A
Single Pulse Avalanche Energy ³		EAS	168.2	mJ
Total Power Dissipation	T _c =25°C	P_D	133	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ¹	$R_{\theta JA}$	42	°C/W
Thermal Resistance from Junction-to-Case	$R_{\theta JC}$	0.94	°C/W

Electrical Characteristics (Tc = 25°C, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	80	-	-	V
Gate-body Leakage current		I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T _J =25°C	I _{DSS}	V _{DS} =80V, V _{GS} = 0V	-	-	1	μA
	T _J =55°C			-	-	100	
Gate-Threshold Voltage		V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	V
Drain-Source on-Resistance ²		R _{DS(on)}	V _{GS} = 10V, I _D = 20A	-	9	12	mΩ
Forward Transconductance ²		g _{fs}	V _{DS} =10V , I _D =20A	-	76	-	S
Dynamic Characteristics							
Input Capacitance		C _{iss}	V _{DS} = 40V, V _{GS} =0V, f =1MHz	-	4150	-	pF
Output Capacitance		C _{oss}		-	220	-	
Reverse Transfer Capacitance		C _{rss}		-	157	-	
Switching Characteristics							
Gate Resistance		R _g	V _{DS} = 0V, V _{GS} =0V, f =1MHz	-	1.1	-	Ω
Total Gate Charge		Q _g	V _{GS} = 10V, V _{DS} = 40V, I _D =20A	-	68.7	-	nC
Gate-Source Charge		Q _{gs}		-	16	-	
Gate-Drain Charge		Q _{gd}		-	22.5	-	
Turn-On Delay Time		t _{d(on)}	V _{GS} =10V, V _{DD} =40V, R _G = 4.7Ω, I _D = 20A	-	35	-	ns
Rise Time		t _r		-	75	-	
Turn-Off Delay Time		t _{d(off)}		-	90	-	
Fall Time		t _f		-	30	-	
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ²		V _{SD}	I _S = 20A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current ^{1,5}		I _S	V _G =V _D =0V, Force Current	-	-	80	A

Notes:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. The EAS data shows Max. rating. The test condition is $V_{DD} = 40V, V_{GS} = 10V, L = 0.4mH, I_{AS} = 29A$.
4. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ C$.
5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

Typical Characteristics

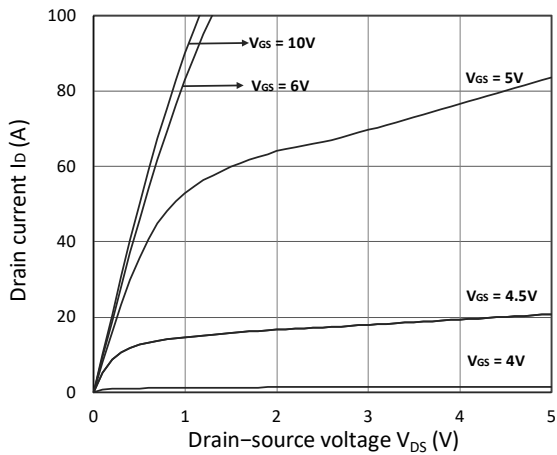


Figure 1. Output Characteristics

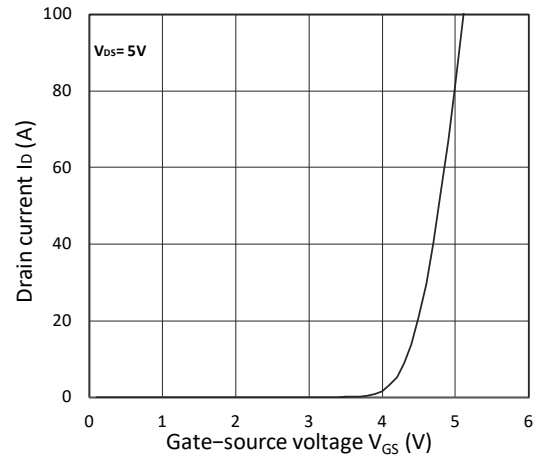


Figure 2. Transfer Characteristics

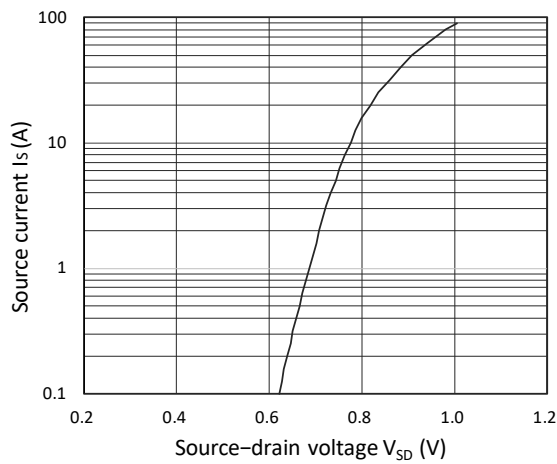
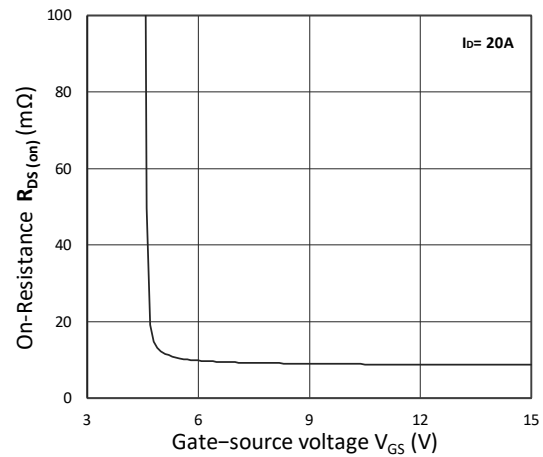
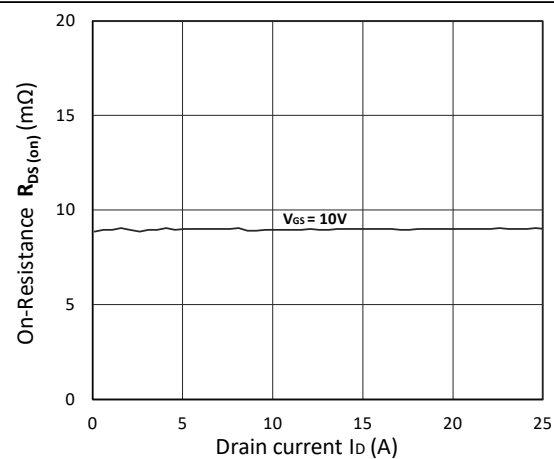
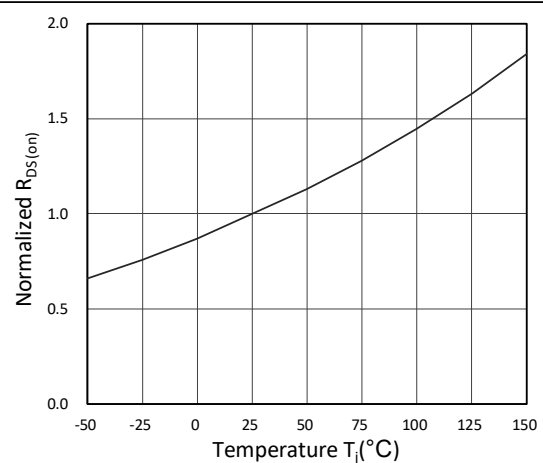


Figure 3. Forward Characteristics of Reverse

Figure 4. $R_{DS(on)}$ vs. V_{GS} Figure 5. $R_{DS(on)}$ vs. I_D Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

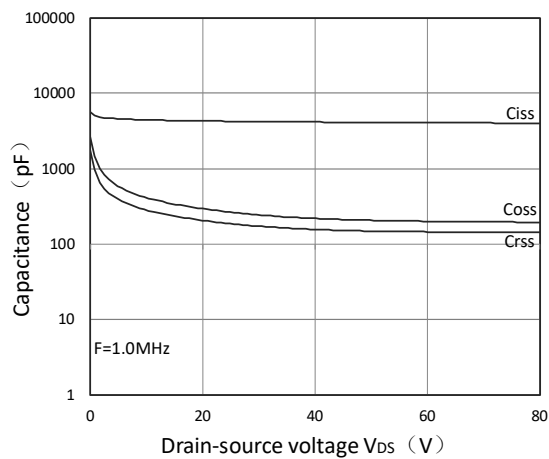


Figure 7. Capacitance Characteristics

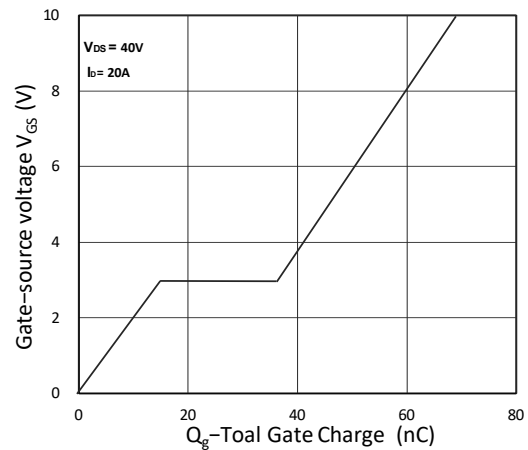


Figure 8. Gate Charge Characteristics

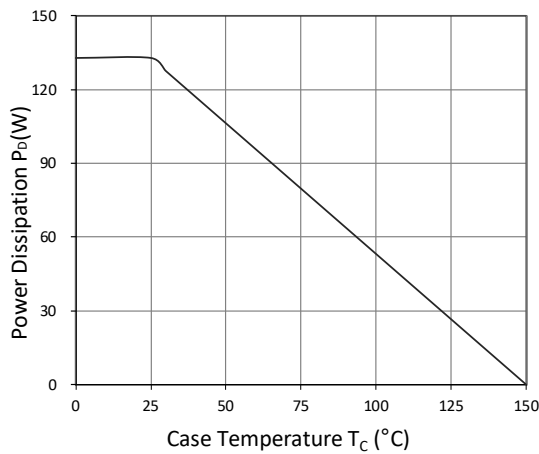


Figure 9. Power Dissipation

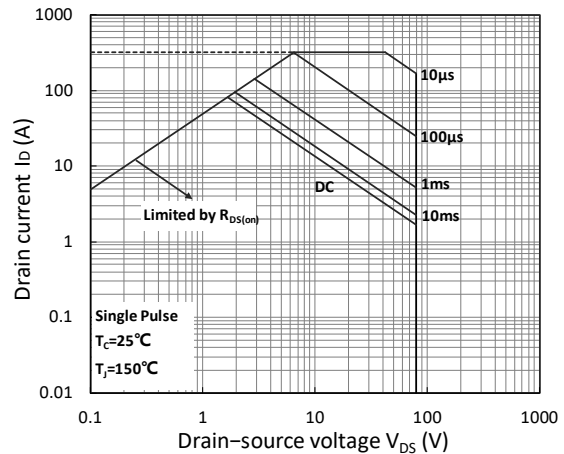


Figure 10. Safe Operating Area

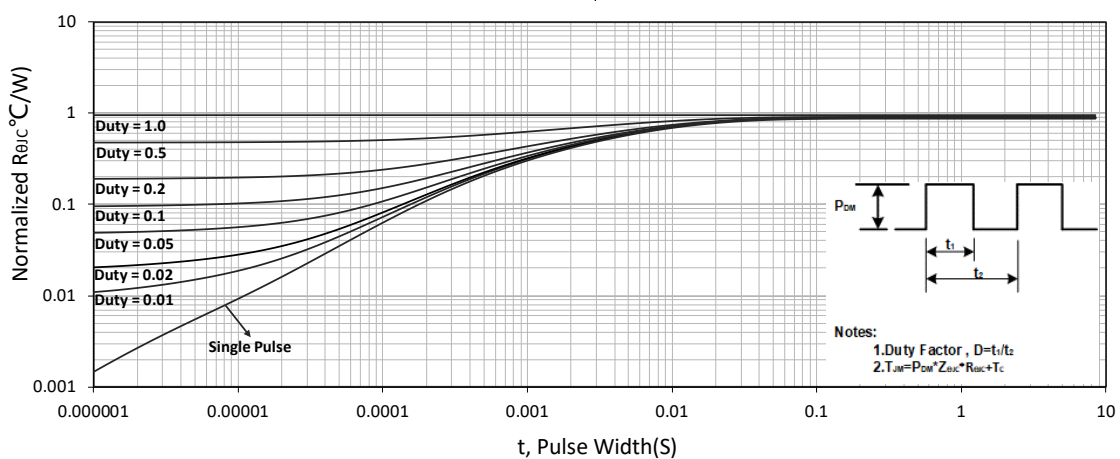


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

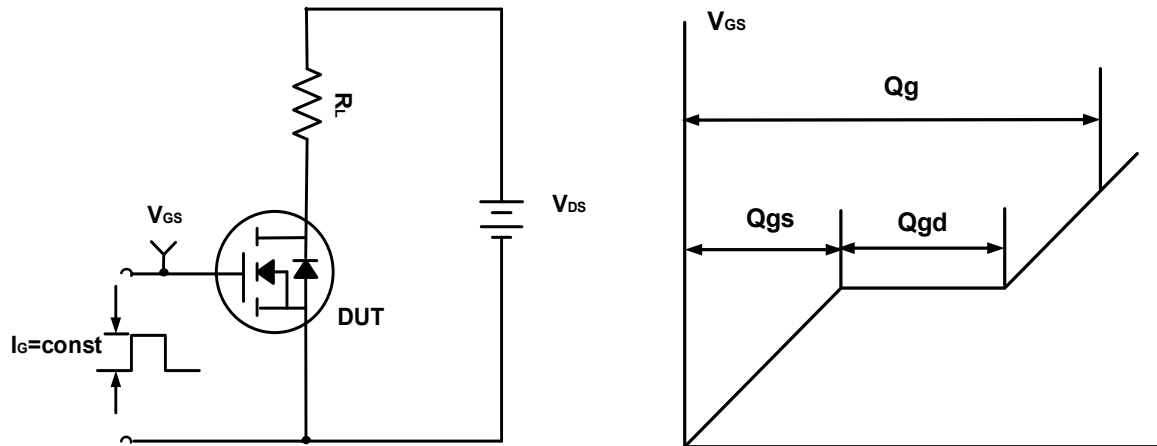


Figure A. Gate Charge Test Circuit & Waveforms

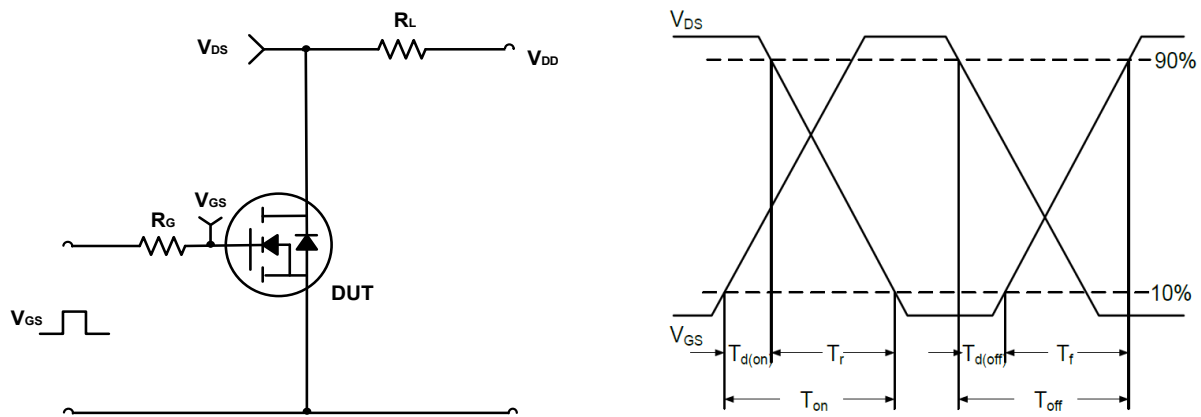


Figure B. Switching Test Circuit & Waveforms

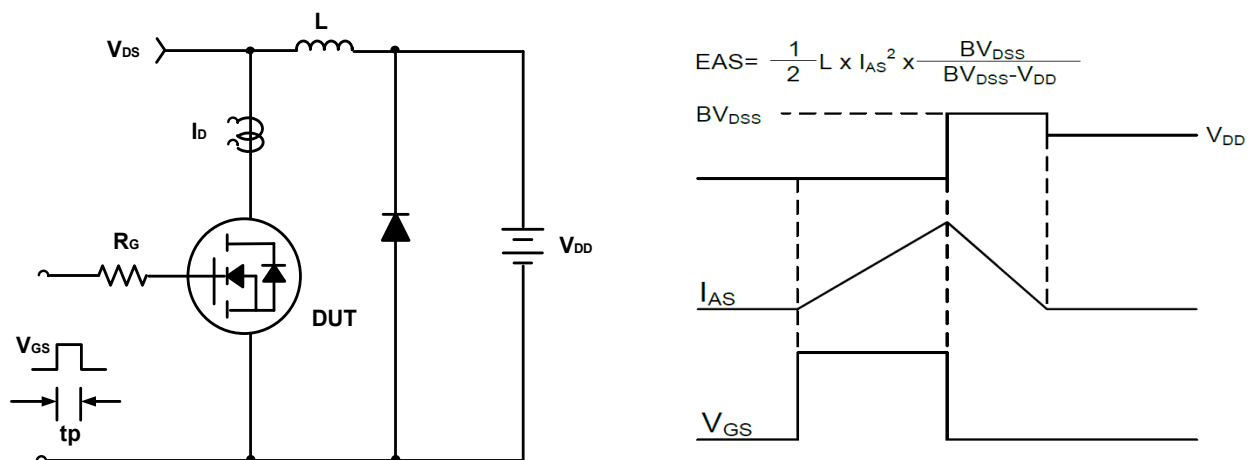
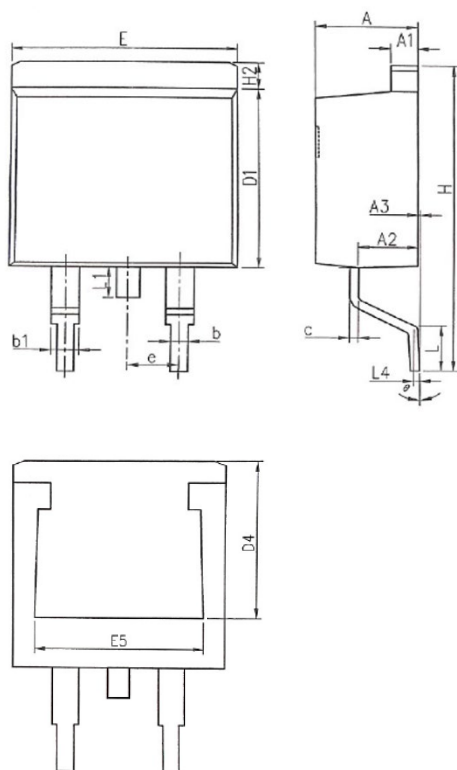


Figure C. Unclamped Inductive Switching Circuit & Waveforms

Mechanical Dimensions for TO-263



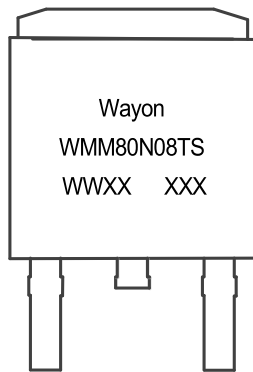
COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	4.37	4.89
A1	1.17	1.42
A2	2.20	2.90
A3	0.00	0.25
b	0.70	0.96
b1	1.17	1.47
c	0.28	0.60
D1	8.45	9.30
D4	6.60	-
E	9.80	10.40
E5	7.06	-
e	2.54BSC	
H	14.70	15.70
H2	1.07	1.47
L	2.00	2.80
L1	-	1.75
L4	0.254BSC	
θ	0°	9°

Ordering Information

Part	Package	Marking	Packing method
WMM80N08TS	TO-263	WMM80N08TS	Tape and Reel

Marking Information



WMM80N08TS = Device code

WWXX XXX= Date code

Contact Information

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